

|                                     |         |                               |
|-------------------------------------|---------|-------------------------------|
| <b>SANYO</b>                        | No.3408 | <b>DSC015</b>                 |
|                                     |         | Silicon Epitaxial Planar Type |
| <b>High-Voltage Switching Diode</b> |         |                               |

**Features**

- Ideally suited for use in hybrid ICs because of small-sized package.
- High breakdown voltage.

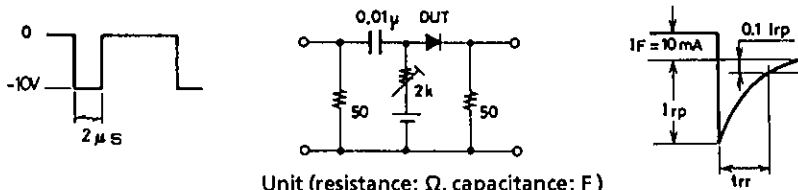
**Absolute Maximum Ratings at Ta = 25°C**

|                                     |            |             |    |      |
|-------------------------------------|------------|-------------|----|------|
| Peak Reverse Voltage                | $V_{RM}$   | 250         | V  | unit |
| Reverse Voltage                     | $V_R$      | 200         | V  |      |
| Surge Forward Current (1 $\mu$ sec) | $I_{FSM}$  | 3           | A  |      |
| Average Rectified Current           | $I_o$      | 150         | mA |      |
| Peak Forward Current                | $I_{FM}$   | 400         | mA |      |
| Allowable Power Dissipation         | $P_d \max$ | 200         | mW |      |
| Junction Temperature                | $T_j$      | 125         | °C |      |
| Storage Temperature                 | $T_{stg}$  | -55 to +125 |    | °C   |

**Electrical Characteristics at Ta = 25°C**

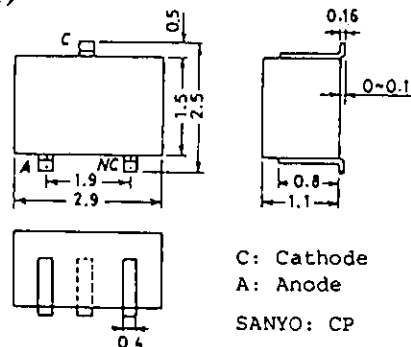
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|---------------------------|----------|---|-----|-----|-----|---------------|
| Forward Voltage           | $V_F$    | $I_F = 100\text{mA}$  | min | typ | max | unit          |
| Reverse Current           | $I_R$    | $V_R = 200\text{V}$   |     |     | 1.0 | V             |
| Interterminal Capacitance | $c$      | $V_R = 0\text{V}, f = 1\text{MHz}$  |     | 4   |     | $\mu\text{A}$ |
| Reverse Recovery Time     | $t_{rr}$ | $I_F = 10\text{mA}, V_R = 10\text{V}, R_L = 50\Omega, I_{rr} = 0.1I_{rp}$ |     | 30  | 200 | ns            |

**Reverse Recovery Time Test Circuit**

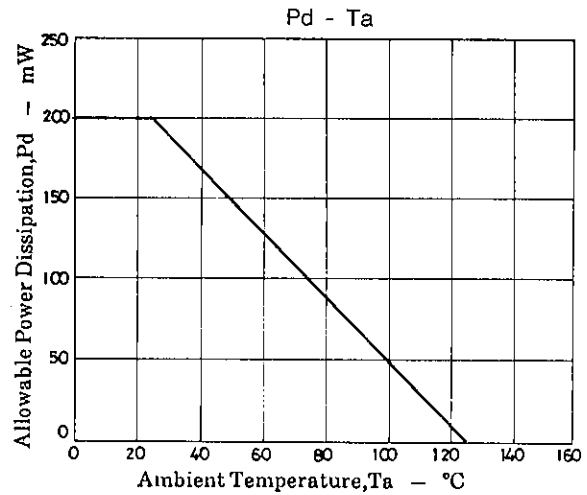
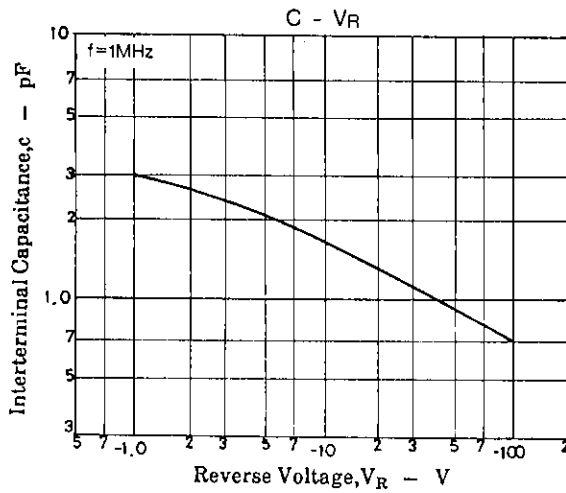
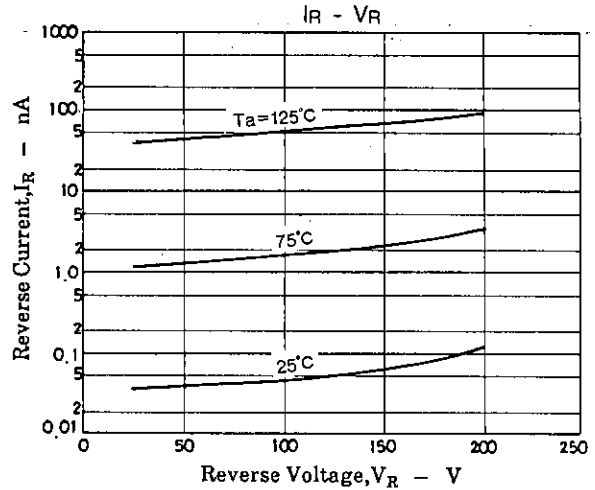
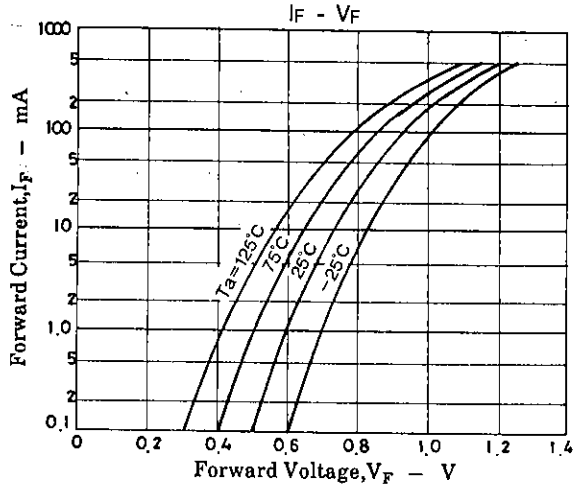


Unit (resistance:  $\Omega$ , capacitance: F)

**Package Dimensions 1148 (unit: mm)**



C: Cathode  
A: Anode  
SANYO: CP



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